

UTC HE8050 NPN EPITAXIAL SILICON TRANSISTOR

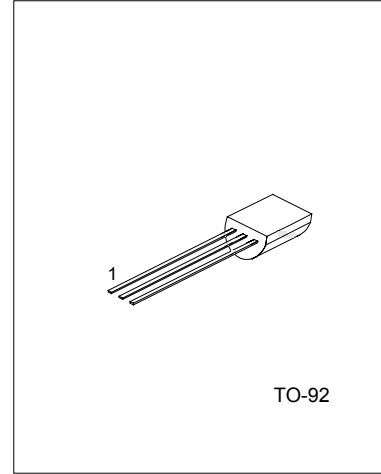
LOW VOLTAGE HIGH CURRENT SMALL SIGNAL NPN TRANSISTOR

DESCRIPTION

The UTC HE8050 is a low voltage high current small signal NPN transistor, designed for Class B push-pull 2W audio amplifier for portable radio and general purpose applications.

FEATURES

- *Collector current up to 1.5A
- *Collector-Emitter voltage up to 25 V
- *complimentary to UTC HE8550



1:EMITTER 2:COLLECTOR 3: BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C ,unless otherwise specified)

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V _{CB0}	40	V
Collector-Emitter Voltage	V _{CEO}	25	V
Emitter-Base Voltage	V _{EB0}	6	V
Collector Dissipation(Ta=25°C)	P _c	1	W
Collector Current	I _c	1.5	A
Junction Temperature	T _j	150	°C
Storage Temperature	T _{STG}	-65 ~ +150	°C

ELECTRICAL CHARACTERISTICS(Ta=25°C,unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CB0}	I _c =100μA,I _E =0	40			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _c =2mA,I _B =0	25			V
Emitter-Base Breakdown Voltage	BV _{EB0}	I _E =100μA,I _c =0	6			V
Collector Cut-Off Current	I _{CB0}	V _{CB} =35V,I _E =0			100	nA
Emitter Cut-Off Current	I _{EB0}	V _{EB} =6V,I _c =0			100	nA
DC Current Gain	h _{FE1}	V _{CE} =1V,I _c =5mA	45	135		
	h _{FE2}	V _{CE} =1V,I _c =100mA	85	160	500	
	h _{FE3}	V _{CE} =1V,I _c =800mA	40	110		
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c =800mA,I _B =80mA			0.5	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _c =800mA,I _B =80mA			1.2	V
Base-Emitter Saturation Voltage	V _{BE}	V _{CE} =1V,I _c =10mA			1.0	V
Current Gain Bandwidth Product	f _T	V _{CE} =10V,I _c =50mA	100			MHz
Output Capacitance	C _{ob}	V _{CB} =10V,I _E =0 f=1MHz		9.0		pF

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CLASSIFICATION OF hFE

RANK	C	D	E
RANGE	120-200	160-300	250-500

TYPICAL PERFORMANCE CHARACTERISTICS

